

Title (en)

METHOD AND DEVICE FOR GAS PHASE DIFFUSION COATING OF METAL COMPONENTS

Title (de)

VERFAHREN UND VORRICHTUNG ZUM GASPHASENDIFFUSIONS BESCHICHTEN VON METALLISCHEN BAUTEILEN

Title (fr)

PROCEDE ET DISPOSITIF POUR LE REVETEMENT PAR DIFFUSION EN PHASE GAZEUSE DE COMPOSANTS METALLIQUES

Publication

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Application

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Abstract (en)

[origin: WO02055754A2] The invention relates to a method and a device for gas phase diffusion coating of components (3), wherein a component surface (4) which is to be coated is brought into contact with a metal halogenide as a coating gas, forming a diffusion layer having a determined thickness and a determined metal content in wt % in the component surface, starting from a nominal concentration of metal halogenide on the component surface leading to a defined coating duration at a defined coating temperature. For the metal halogenide, a first concentration which is higher than the nominal concentration and at least one second concentration which is lower than the nominal concentration are adjusted on the surface (4) over a first period of time and at least a second period of time. The first and the at least one second period of time are chosen in such a way that the sum thereof is shorter than the coating duration with the nominal concentration.

IPC 8 full level

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